



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-220 Plastic-Encapsulate Transistors

2SB1185 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 2 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -3 A

Collector-base voltage

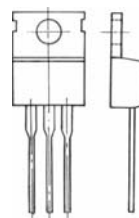
$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-220

1. BASE
2. COLLECTOR
3. EMITTER



1 2 3

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu A, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$			-1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-3V, I_C=-0.5A$	60		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2A, I_B=-0.2A$			-1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-2A, I_B=-0.2A$			-1.5	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-0.5A, f=30MHz$		70		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		50		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	D	E	F
Range	60-120	100-200	160-320
Marking			